## Contents

Preface XV

	List of Contributors XVII  Color Plates XXIII
Part One	Scaling and Challenge of Si-based CMOS 1
1	Scaling and Limitation of Si-based CMOS 3
	Gang He, Zhaoqi Sun, Mao Liu, and Lide Zhang
1.1	Introduction 3
1.2	Scaling and Limitation of CMOS 4
1.2.1	Device Scaling and Power Dissipation 4
1.2.2	Gate Oxide Tunneling 7
1.2.3	Gate Oxide Scaling Trends 8
1.2.4	Scaling and Limitation of SiO <sub>2</sub> Gate Dielectrics 10
1.2.5	Silicon Oxynitrides 14
1.3	Toward Alternative Gate Stacks Technology 16
1.3.1	Advances and Challenges in Dielectric Development 16
1.3.2	Advances and Challenges in Electrode Development 19
1.4	Improvements and Alternative to CMOS Technologies 22
1.4.1	Improvement to CMOS 22
1.4.1.1	New Materials 22
1.4.1.2	New Structures 23
1.5	Potential Technologies Beyond CMOS 23
1.6	Conclusions 24
	References 25
Part Two	High-k Deposition and Materials Characterization 31
2	Issues in High-k Gate Dielectrics and its Stack Interfaces 33
	Hong-Liang Lu and David Wei Zhang
2.1	Introduction 33
2.2	High-k Dielectrics 33
2.2.1	The Criteria Required for High-k Dielectrics 34



۷١	Contents	
·	2.2.2	The Challenges of High-k Dielectrics 37
	2.2.2.1	Structural Defects 37
	2.2.2.2	Channel Mobility Degradation 38
	2.2.2.3	Threshold Voltage Control 38
	2.2.2.4	Reliability 39
	2.3	Metal Gates 40
	2.3.1	Basic Requirements for Metal Gates 41
	2.3.2	Metal Gate Materials 41
	2.3.2.1	Pure Metals 42
	2.3.2.2	Metallic Alloys 42
	2.3.2.3	Metal Nitrides 42
	2.3.2.4	Metal Silicides 43
	2.3.3	Work Function 43
	2.3.4	Metal Gate Structures 44
	2.3.5	Metal Gate/High-k Integration 44
	2.3.6	Process Integration 44
	2.4	Integration of High-k Gate Dielectrics with Alternative
		Channel Materials 45
	2.4.1	High-k/Ge Interface 46
	2.4.2	High-k/III–V Interface 49
	2.5	Summary 51
		References 52
	3	UV Engineering of High-k Thin Films 61
		Ian W. Boyd
	3.1	Introduction 61
	3.2	Gas Discharge Generation of UV (Excimer) Radiation 61
	3.3	Excimer Lamp Sources Based on Silent Discharges 63
	3.4	Predeposition Surface Cleaning for High-k Layers 65
	3.5	UV Photon Deposition of Ta <sub>2</sub> O <sub>5</sub> Films 66
	3.6	Photoinduced Deposition of $Hf_{1-x}Si_xO_y$ Layers 70
	3.7	Summary 73
		References 73
	4	Atomic Layer Deposition Process of Hf-Based High-k Gate
		Dielectric Film on Si Substrate 77
		Tae Joo Park, Moonju Cho, Hyung-Suk Jung, and Cheol Seong Hwang
	4.1	Introduction 77
	4.2	Precursor Effect on the HfO <sub>2</sub> Characteristics 78
	4.2.1	Hafnium Precursor Effect on the HfO <sub>2</sub> Dielectric Characteristics 78
	4.2.1.1	Hafnium Chloride (HfCl <sub>4</sub> ) 78
	4.2.1.2	Tetrakis Dimethylamido Hafnium [HfN(CH <sub>3</sub> ) <sub>2</sub> ] <sub>4</sub> 82
	4.2.1.3	Tetrakis Ethylmethylamino Hafnium (Hf[N(C <sub>2</sub> H <sub>5</sub> )(CH <sub>3</sub> )] <sub>4</sub> ) 85
	4.2.1.4	tert-Butoxytris[Ethylmethylamido] Hafnium (HfO <sup>t</sup> Bu[NEtMe] <sub>3</sub> ) 86
	4.2.1.5	tert-Butoxide Hafnium (Hf[OC <sub>4</sub> H <sub>9</sub> ] <sub>4</sub> ) 87

4.2.2	Oxygen Sources and Reactants 88
4.2.2.1	H <sub>2</sub> O versus O <sub>3</sub> 88
4.2.2.2	O <sub>3</sub> Concentration 93
4.2.2.3	Reactants for In Situ N Incorporation 95
4.3	Doped and Mixed High-k 97
4.3.1	Zr-Doped HfO <sub>2</sub> 98
4.3.2	Si-Doped HfO <sub>2</sub> 100
4.3.3	Al-Doped HfO <sub>2</sub> 102
4.4	Summary 105
	References 105
5	Structural and Electrical Characteristics of Alternative
	High-κ Dielectrics for CMOS Applications 111
	Fu-Chien Chiu, Somnath Mondal, and Tung-Ming Pan
5.1	Introduction 111
5.2	Requirement of High-k Oxide Materials 114
5.3	Rare-Earth Oxide as Alternative Gate Dielectrics 117
5.4	Structural Characteristics of High- $\kappa$ RE Oxide
	Films 118
5.4.1	Process Compatibility 118
5.4.2	X-Ray Diffraction Analysis 120
5.4.3	Atomic Force Microscope Investigation 122
5.4.4	Transmission Electron Microscopy Technique 125
5.4.5	X-Ray Photoelectron Spectroscopy Analysis 128
5.5	Electrical Characteristics of High-κ RE Oxide Films 132
5.5.1	The Threshold Voltage, Flatband Voltage, Interface Trap,
	and Fixed Charge 132
5.5.2	Leakage Mechanism 134
5.5.2.1	Schottky or Thermionic Emission 135
5.5.2.2	Fowler–Nordheim Tunneling 137
5.5.2.3	Direct Tunneling 139
5.5.2.4	Thermionic Field Emission 141
5.5.2.5	Poole–Frenkel Emission 141
5.5.2.6	Hopping Conduction 142
5.5.2.7	Ohmic Conduction 144
5.5.2.8	Space Charge-Limited Conduction 145
5.5.2.9	Ionic Conduction 149
5.5.2.10	Grain Boundary-Limited Conduction 149
5.5.3	High-κ Silicon Interface 150
5.5.4	Band Alignment 153
5.5.5	Channel Mobility 163
5.5.6	Dielectric Breakdown 166
5.6	Conclusions and Perspectives 171
	References 172

VIII	Contents
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6	Hygroscopic Tolerance and Permittivity Enhancement of Lanthanum Oxide (La <sub>2</sub> O <sub>3</sub> ) for High-k Gate Insulators 185
	Yi Zhao
6.1	Introduction 185
6.2	Hygroscopic Phenomenon of La <sub>2</sub> O <sub>3</sub> Films 186
6.2.1	Effect of Moisture Absorption on Surface Roughness of La <sub>2</sub> O <sub>3</sub> Films 187
6.2.2	Effect of Moisture Absorption on Electrical Properties of La <sub>2</sub> O <sub>3</sub> Films 188
6.3	Low Permittivity Phenomenon of La <sub>2</sub> O <sub>3</sub> Films 191
6.3.1	Moisture Absorption-Induced Permittivity Degradation of $La_2O_3$ Films 191
6.3.2	Permittivity of La <sub>2</sub> O <sub>3</sub> Films without Moisture Absorption 193
6.4	Hygroscopic Tolerance Enhancement of La <sub>2</sub> O <sub>3</sub> Films 194
6.4.1	Hygroscopic Tolerance Enhancement of La <sub>2</sub> O <sub>3</sub> Films by Y <sub>2</sub> O <sub>3</sub> Doping 194
6.5	Hygroscopic Tolerance Enhancement of La <sub>2</sub> O <sub>3</sub> Films by Ultraviolet Ozone Treatment 198
6.6	Thermodynamic Analysis of Moisture Absorption Phenomenon in High-k Gate Dielectrics 203
6.7	Permittivity Enhancement of La <sub>2</sub> O <sub>3</sub> Films by Phase Control 205
6.7.1	Experimental Procedures and Characterizations 207
6.7.2	Permittivity Enhancement by Phase Control due to Y <sub>2</sub> O <sub>3</sub> Doping 208
6.7.3	Higher-k Amorphous La <sub>1-x</sub> Ta <sub>x</sub> O <sub>y</sub> Films 213
6.8	Summary 219
	References 221
7	Characterization of High-k Dielectric Internal Structure by
	X-Ray Spectroscopy and Reflectometry: New Approaches to Interlayer Identification and Analysis 225
	Elena O. Filatova, Andrey A. Sokolov, and Igor V. Kozhevnikov
7.1	Introduction 225
7.2	Chemical Bonding and Crystalline Structure of Transition
7.2	Metal Dielectrics 227
7.3	NEXAFS Investigation of Internal Structure 229
7.4	Studying the Internal Structure of High-K Dielectric Films by
	Hard X-Ray Photoelectron Spectroscopy and TEM 236
7.5	Studying the Internal Structure of High-K Dielectric Films by X-ray Reflectometry 244
7.5.1	Reconstruction of the Dielectric Constant Profile by Hard X-Ray Reflectometry 244
7.5.2	Reconstruction of the Depth Distribution of Chemical Elements Concentration by Soft X-Ray Reflectometry 254 References 266

8	High-k Insulating Films on Semiconductors and Metals: General
	Trends in Electron Band Alignment 273
	Valeri V. Afanas'ev, Michel Houssa, and Andre Stesmans
8.1	Introduction 273
8.2	Band Offsets and IPE Spectroscopy 274
8.3	Silicon/Insulator Band Offsets 277
8.4	Band Alignment at Interfaces of High-Mobility
	Semiconductors 280
8.5	Metal/Insulator Barriers 284
8.6	Conclusions 289
	References 289
Part Three	e Challenge in Interface Engineering and Electrode 293
9	Interface Engineering in the High-k Dielectric Gate Stacks 295
	Shijie Wang, Yuanping Feng, and Alfred C.H. Huan
9.1	Introduction 295
9.2	High-k Oxide/Si Interfaces 295
9.2.1	Growth of Crystalline High-k Oxide on Semiconductors 297
9.2.2	Measurement of Band Alignment at High-k Oxide/Si Interfaces 298
9.3	Metal Gate/High-k Dielectric Interfaces 303
9.4	Chemical Tuning of Band Alignments for Metal Gate/High-k
	Oxide Interfaces 308
9.5	Summary and Discussion 314
	References 315
10	Interfacial Dipole Effects on High-k Gate Stacks 319
	Li Qiang Zhu
10.1	Introduction 319
10.2	Metal Gate Consideration 321
10.3	Interfacial Dipole Effects in High-k Gate Stacks 324
10.3.1	Modification of the Gate Work Function by the Interfacial Dipole 324
10.3.2	Fermi-Level Pinning Effects at Gate/High-k Interfaces 326
10.3.3	Micromodels for the Interfacial Dipole in High-k Stacks 328
10.3.3.1	Fermi-Level Pinning 328
10.3.3.2	Oxygen Vacancy Model 329
10.3.3.3	Pauling Electronegativity Model 330
10.3.3.4	Area Oxygen Density Model 331
10.4	Observation of the Interfacial Dipole in High-k Stacks 332
10.4.1	Flatband Voltage Shifts in Capacitance-Voltage Measurements 333
10.4.2	Core-Level Binding Energy Shift in Photoelectron
	Spectroscopy 335
10.4.2.1	Band Discontinuities and Schottky Barrier Analysis in
	Heterostructures 336
10.4.2.2	Interfacial Charge Investigation 337

x	Contents	
	10.4.2.3	Band Alignment Determination 337
	10.4.2.4	Interfacial Dipole Measurement by Photoelectron Spectroscopy 339
	10.4.3	Band Alignments Measured by Using Internal Photoemission 345
	10.4.4	Potential Shifts in Kelvin Probe Measurements 346
	10.5	Summary 348
		References 349
	11	Metal Gate Electrode for Advanced CMOS Application 355
		Wenwu Wang, Xiaolei Wang, and Kai Han
	11.1	The Scaling and Improved Performance of MOSFET Devices 355
	11.2	Urgent Issues about MOS Gate Materials for Sub-0.1 $\mu m$
		Device Gate Stack 360
	11.2.1	SiO <sub>2</sub> Gate Dielectric 360
	11.2.2	Polysilicon Electrode 363
	11.3	New Requirements of MOS Gate Materials for Sub-0.1 μm
		Device Gate Stack 365
	11.3.1	High-κ Gate Dielectric 365
	11.3.2	Metal Gate Electrode 367
	11.4	Summary 374
		References 374
	Part Four	Development in non-Si-based CMOS technology 379
		,
	12	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381
		Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381 Albert Achin
	12.1	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin  Introduction 381
	12.1 12.2	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin Introduction 381  High-κ/Si CMOSFETs 386
	12.1 12.2 12.2.1	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin  Introduction 381  High-κ/Si CMOSFETs 386  Potential Interface Reaction Mechanism 387
	12.1 12.2 12.2.1 12.2.2	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin  Introduction 381  High-κ/Si CMOSFETs 386  Potential Interface Reaction Mechanism 387  Inserting an Ultrathin SiON 388
	12.1 12.2 12.2.1 12.2.2 12.2.3	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin  Introduction 381  High-κ/Si CMOSFETs 386  Potential Interface Reaction Mechanism 387  Inserting an Ultrathin SiON 388  Low-Temperature Process 389
	12.1 12.2 12.2.1 12.2.2	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin  Introduction 381  High-κ/Si CMOSFETs 386  Potential Interface Reaction Mechanism 387  Inserting an Ultrathin SiON 388
	12.1 12.2 12.2.1 12.2.2 12.2.3 12.3 12.3	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin Introduction 381  High-κ/Si CMOSFETs 386  Potential Interface Reaction Mechanism 387 Inserting an Ultrathin SiON 388  Low-Temperature Process 389  High-κ/Ge CMOSFETs 392  Defect-Free Ge-on-Insulator 392
	12.1 12.2 12.2.1 12.2.2 12.2.3 12.3	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin Introduction 381  High-κ/Si CMOSFETs 386  Potential Interface Reaction Mechanism 387 Inserting an Ultrathin SiON 388  Low-Temperature Process 389  High-κ/Ge CMOSFETs 392  Defect-Free Ge-on-Insulator 392  The Challenge for Ge n-MOS 394
	12.1 12.2 12.2.1 12.2.2 12.2.3 12.3 12.3	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin Introduction 381  High-κ/Si CMOSFETs 386  Potential Interface Reaction Mechanism 387 Inserting an Ultrathin SiON 388  Low-Temperature Process 389  High-κ/Ge CMOSFETs 392  Defect-Free Ge-on-Insulator 392  The Challenge for Ge n-MOS 394
	12.1 12.2 12.2.1 12.2.2 12.2.3 12.3 12.3	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin Introduction 381  High-κ/Si CMOSFETs 386  Potential Interface Reaction Mechanism 387 Inserting an Ultrathin SiON 388  Low-Temperature Process 389  High-κ/Ge CMOSFETs 392  Defect-Free Ge-on-Insulator 392  The Challenge for Ge n-MOS 394  High-Mobility Ge n-MOS Using Novel Technology 395
	12.1 12.2 12.2.1 12.2.2 12.2.3 12.3 12.3	Metal Gate/High- $\kappa$ CMOS Evolution from Si to Ge Platform 381  Albert Achin Introduction 381  High- $\kappa$ /Si CMOSFETs 386  Potential Interface Reaction Mechanism 387 Inserting an Ultrathin SiON 388  Low-Temperature Process 389  High- $\kappa$ /Ge CMOSFETs 392  Defect-Free Ge-on-Insulator 392  The Challenge for Ge n-MOS 394  High-Mobility Ge n-MOS Using Novel Technology 395  Ge Platform 397
	12.1 12.2 12.2.1 12.2.2 12.2.3 12.3 12.3	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin Introduction 381  High-κ/Si CMOSFETs 386  Potential Interface Reaction Mechanism 387 Inserting an Ultrathin SiON 388  Low-Temperature Process 389  High-κ/Ge CMOSFETs 392  Defect-Free Ge-on-Insulator 392  The Challenge for Ge n-MOS 394  High-Mobility Ge n-MOS Using Novel Technology 395  Ge Platform 397  Logic and Memory Integration 397
	12.1 12.2 12.2.1 12.2.2 12.2.3 12.3 12.3	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin Introduction 381  High-κ/Si CMOSFETs 386  Potential Interface Reaction Mechanism 387 Inserting an Ultrathin SiON 388  Low-Temperature Process 389  High-κ/Ge CMOSFETs 392  Defect-Free Ge-on-Insulator 392  The Challenge for Ge n-MOS 394  High-Mobility Ge n-MOS Using Novel Technology 395  Ge Platform 397  Logic and Memory Integration 397  3D GeOI/Si IC 400
	12.1 12.2 12.2.1 12.2.2 12.2.3 12.3 12.3	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin Introduction 381  High-κ/Si CMOSFETs 386  Potential Interface Reaction Mechanism 387 Inserting an Ultrathin SiON 388  Low-Temperature Process 389  High-κ/Ge CMOSFETs 392  Defect-Free Ge-on-Insulator 392  The Challenge for Ge n-MOS 394  High-Mobility Ge n-MOS Using Novel Technology 395  Ge Platform 397  Logic and Memory Integration 397  3D GeOI/Si IC 400  Conclusions 401
	12.1 12.2 12.2.1 12.2.2 12.2.3 12.3 12.3	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin Introduction 381  High-κ/Si CMOSFETs 386  Potential Interface Reaction Mechanism 387 Inserting an Ultrathin SiON 388  Low-Temperature Process 389  High-κ/Ge CMOSFETs 392  Defect-Free Ge-on-Insulator 392  The Challenge for Ge n-MOS 394  High-Mobility Ge n-MOS Using Novel Technology 395  Ge Platform 397  Logic and Memory Integration 397  3D GeOI/Si IC 400  Conclusions 401  References 402
	12.1 12.2 12.2.1 12.2.2 12.2.3 12.3 12.3	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin Introduction 381  High-κ/Si CMOSFETs 386  Potential Interface Reaction Mechanism 387 Inserting an Ultrathin SiON 388  Low-Temperature Process 389  High-κ/Ge CMOSFETs 392  Defect-Free Ge-on-Insulator 392  The Challenge for Ge n-MOS 394  High-Mobility Ge n-MOS Using Novel Technology 395  Ge Platform 397  Logic and Memory Integration 397  3D GeOI/Si IC 400  Conclusions 401  References 402  Theoretical Progress on GaAs (001) Surface and GaAs/high-κ Interface 407
	12.1 12.2 12.2.1 12.2.2 12.2.3 12.3 12.3	Metal Gate/High-κ CMOS Evolution from Si to Ge Platform 381  Albert Achin Introduction 381  High-κ/Si CMOSFETs 386  Potential Interface Reaction Mechanism 387 Inserting an Ultrathin SiON 388  Low-Temperature Process 389  High-κ/Ge CMOSFETs 392  Defect-Free Ge-on-Insulator 392  The Challenge for Ge n-MOS 394  High-Mobility Ge n-MOS Using Novel Technology 395  Ge Platform 397  Logic and Memory Integration 397  3D GeOI/Si IC 400  Conclusions 401  References 402  Theoretical Progress on GaAs (001) Surface and GaAs/high-κ Interface 407  Weichao Wang, Ka Xiong, Robert M. Wallace, and Kyeongjae Cho

13.3.1	Clean GaAs Surface 409
13.3.2	GaAs Surface Oxidation 411
13.3.3	Passivation of the Oxidized GaAs Surface 415
13.3.4	Initial oxidation of the GaAs(001)- $\beta$ 2(2 × 4) Surface 418
13.4	Origin of Gap States at the High-k/GaAs Interface and Interface Passivation 419
13.4.1	Strained HfO <sub>2</sub> /GaAs Interface 419
13.4.2	Strain-Free GaAs/HfO <sub>2</sub> Interfaces 421
13.4.3	Si Passivation of HfO <sub>2</sub> /GaAs Interface 423
13.4.4	Sulfur Passivation Effect on HfO <sub>2</sub> /GaAs Interface 425
13.5	Conclusions 428 References 428
14	III–V MOSFETs with ALD High-κ Gate Dielectrics 433 Jack C. Lee and Han Zhao
14.1	Introduction 433
14.2	Surface Channel InGaAs MOSFETs with ALD Gate Oxides 436
14.2.1	Effects of Gate-First and Gate-Last Processes on Interface Quality of In <sub>0.53</sub> Ga <sub>0.47</sub> As MOSCAPs Using ALD Al <sub>2</sub> O <sub>3</sub> and HfO <sub>2</sub> 436
14.2.2	Effect of Channel Doping Concentration and Thickness on Device Performance for In <sub>0.53</sub> Ga <sub>0.47</sub> As MOSFETs with ALD Al <sub>2</sub> O <sub>3</sub> Dielectrics 441
14.2.3	In <sub>0.53</sub> Ga <sub>0.47</sub> As n-MOSFETs with ALD Al <sub>2</sub> O <sub>3</sub> , HfO <sub>2</sub> , and LaAlO <sub>3</sub> Gate Dielectrics 445
14.3	Buried Channel InGaAs MOSFETs 450
14.3.1	High-Performance In <sub>0.7</sub> Ga <sub>0.3</sub> As MOSFETs with
	Mobility >4400 cm <sup>2</sup> /(V s) Using InP Barrier Layer 450
14.3.2	Effects of Barrier Layers on Device Performance of High-Mobility $In_{0.7}$ $Ga_{0.3}$ As MOSFETs 455
14.4	Summary 460
	References 466
Part Five	High-k Application in Novel Devices 471
15	High-k Dielectrics in Ferroelectric Gate Field Effect Transistors for Nonvolatile Memory Applications 473  Xubing Lu
15.1	Introduction 473
15.2	Overview of High-k Dielectric Studies for FeFET Applications 477
15.2.1	Materials Requirements for High-k Buffer Layers 477
15.2.2	Research Progress of High-k in the MFIS Devices 478
15.2.3	Issues for High-k Dielectric Integration into MFIS Devices 481
15.2.3.1	High-k/Si Interfacial Reaction 481
15.2.3.2	Crystallinity and Interdiffusion with Ferroelectric Film 484
15.2.3.3	Possible Solutions 484

ХII	Contents	
·	15.3	Developing of HfTaO Buffer Layers for FeFET Applications 485
	15.3.1	Introduction 485
	15.3.2	Experimental Procedure 485
	15.3.3	Crystallization Characteristics of HfTaO Films 486
	15.3.4	Electrical Properties of Hf/TaO Films on Si Substrates 486
	15.3.5	Electrical Characteristics of Pt/SBT/HfTaO/Si Diodes 490
	15.3.6	Electrical Properties of MFIS FeFETs with HfTaO
		Buffer Layers 493
	15.4	Summary 496
		References 497
	16	Rare-Earth Oxides as High-k Gate Dielectrics for Advanced
		Device Architectures 501
		Pooi See Lee, Mei Yin Chan, and Peter Damarwan
	16.1	Introduction 501
	16.2	Key Challenges for High-k Dielectrics 502
	16.2.1	Interfaces Properties 502
	16.2.2	Thermal Stability 502
	16.2.3	Fermi-Level Pinning 503
	16.2.4	Device Integration 503
	16.3	Rare-Earth Oxides as High- $\kappa$ Dielectrics 506
	16.3.1	Lutetium Oxides as High-k Dielectrics 507
	16.3.2	$Gd_2O_3$ as High- $\kappa$ Dielectric 514
	16.3.3	Summary 516
	16.4	High- <i>k</i> Dielectrics in Advanced Device Architecture 517
	16.4.1	HfO <sub>2</sub> Alloy with Rare-Earth and Bilayer Stacks 517
	16.4.2	Advanced Device Architecture with High-k Dielectrics 519
	16.4.2.1	High-k Dielectrics for Advanced CNT and
		Nanowire Devices 519
	16.4.2.2	High-k Dielectrics for DRAM and Flash Memory
		Devices 520
		References 522
	Part Six	Challenge and Future Directions 531
	17	The Interaction Challenges with Novel Materials in Developing
		High-Performance and Low-Leakage High-κ/Metal Gate
		CMOS Transistors 533
		Michael Chudzik, Siddarth Krishnan, Unoh Kwon, Mukesh Khare, Vijay
		Narayanan, Takashi Ando, Ed Cartier, Huiming Bu, and Vamsi Paruchuri
	17.1	Introduction 533
	17.2	Traditional CMOS Integration Processes 534
	17.3	High- $\kappa$ /Metal Gate Integration Processes 536
	17 4	Mobility 536

Metal Electrodes and Effective Work Function 541

17.5

$T_{ m inv}$ Scaling and Impacts on Gate Leakage and Effective
Work Function 544
Ambients and Oxygen Vacancy-Induced Modulation of
Threshold Voltage 545
Reliability 547
Conclusions 550
References 551

Index 557